

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

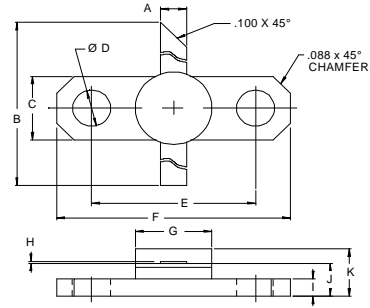
The **ASI AVF150** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	11 A
V_{CC}	55 V
P_{DISS}	400 W @ T _C = 25 °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.6 °C/W

PACKAGE STYLE .250 2L FLG (B)


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

ORDER CODE: ASI10570
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	65			V
BV_{CER}	I _C = 15 mA R _{BE} = 10 Ω	65			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CES}	V _{CE} = 50 V			12.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	15		120	---
P_G	V _{CC} = 43 V P _{OUT} = 150 W f = 1030 - 1090	8.5			dB
η_C	MHZ	40			%